

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-2. (Cancelled)

3. (Currently Amended) The method of Claim 2_18, wherein the thin film is applied to the front surface of the semiconductor wafer.

4. (Currently Amended) The method of Claim +18 wherein the thin film comprises a film of dry photosensitive resin.

5. (Original) The method of Claim 4, wherein the thin film is of the type known commercially by the name RISTON®.

6-7. (Cancelled)

8. (Currently Amended) The method of Claim +18, wherein the micro-mechanism comprises an electrostatic micro-actuator used for the fine positioning of a reading/writing transducer in a hard-disk reading/writing unit.

9. (Cancelled)

10. (Currently Amended) The method of Claim 9_18, wherein forming the hard-mask comprises depositing a layer of silicon dioxide or aluminum on the thin-dry film at low temperature and selectively removing the sacrificial layer comprises selectively removing the silicon dioxide or aluminum layer by a photolithographic technique.

11. (Cancelled)

12. (Currently Amended) The method of Claim-11 22, further comprising the mounting of a respective reading/writing transducer on each die.

13. (Currently Amended) The method of Claim-10 18, further comprising, ~~after the definition of the electrical connection elements~~ gluing a respective reading/writing transducer onto each micro-actuator component and soldering terminals of the transducer to the electrical connection elements of the respective micro-actuator micro-mechanism, and then dividing the semiconductor wafer with the transducers mounted by cutting it into a plurality of individual dice.

14-17. (Cancelled)

18. (Currently Amended) A method of producing suspended elements between two portions of a micro-mechanism containing components that move relative to one another on a semiconductor wafer, the method comprising:

applying the adhesive side of a dry film over the micro-mechanism on the semiconductor wafer to immobilize the moveable components without penetrating any cavities therein;

forming a mask on the dry film;

depositing, developing, and selectively removing a sacrificial layer from the mask and the dry film to form windows on the dry film, the dry film protecting the cavities from infiltration of liquids during the developing step;

opening the windows by selectively etching the dry film;

depositing a dielectric layer to cover the windows without penetrating any underlying cavities;

depositing a conductive layer that is attached to at least one moveable portion of the micro-mechanism; and

selectively removing the conductive layer and the dielectric layer, and removing the dry film to form electrical connection elements suspended between the two portions of the micro-mechanism containing components that move relative to one another.

19. (Original) The method of Claim 18, wherein applying the adhesive side of a dry film further comprises reducing the thickness of the wafer after the dry film has been applied.

20. (Original) The method of Claim 18, wherein applying the adhesive side of a dry film comprises a subsequent step of applying a second adhesive layer to a back surface of the semiconductive wafer, the second adhesive layer having an exposed adhesive surface.

21. (Original) The method of Claim 18, further comprising removing the dry film to release the moveable components.

22. (Original) The method of Claim 21, further comprising, after selectively removing the conductive layer and the dielectric layer and before removing the dry film:

- dividing the wafer into dice;
- attaching a slider to each die;
- gluing the die and the attached slider to a gimbal; and
- attaching wires to the die.

23. (Original) The method of Claim 21, wherein removing the dry film comprises removing the dry film by oxygen plasma etching.

24. (Original) The method of Claim 21, wherein removing the dry film comprises removing the dry film by immersion in a bath of NaOH.